

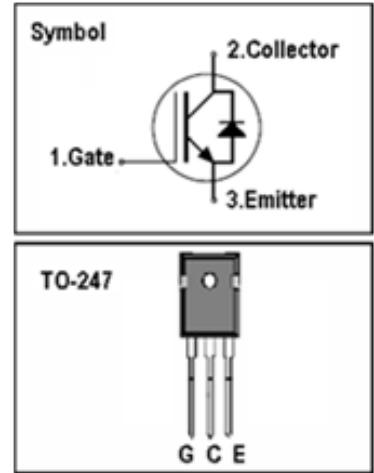
## IGBT

### Features

- 650V,30A
- $V_{CE(sat)(typ.)}=2.0V@V_{GE}=15V,I_C=30A$
- High speed switching
- Higher system efficiency
- Soft current turn-off waveforms
- Square RBSOA

### General Description

JIAEN Trench IGBTs offer lower losses and higher energy efficiency for application such as Motor control, general inverter and other soft switching applications.



### Absolute Maximum Ratings

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	650	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 30$	V
$I_C$	Continuous Collector Current ( $T_C=25^\circ C$ )	60	A
	Continuous Collector Current ( $T_C=100^\circ C$ )	30	A
$I_{CM}$	Pulsed Collector Current (Note 1)	90	A
$I_F$	Diode Continuous Forward Current ( $T_C=100^\circ C$ )	30	A
$I_{FM}$	Diode Maximum Forward Current (Note 1)	90	A
$t_{sc}$	Short Circuit Withstand Time	10	us
$P_D$	Maximum Power Dissipation ( $T_C=25^\circ C$ )	297	W
	Maximum Power Dissipation ( $T_C=100^\circ C$ )	119	W
$T_J$	Operating Junction Temperature Range	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th\ j-c}$	Thermal Resistance, Junction to case for IGBT	0.42	$^\circ C/W$
$R_{th\ j-c}$	Thermal Resistance, Junction to case for Diode	1.4	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  unless otherwise noted )

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	650	-	-	V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{CE}=650V, V_{GE}=0V$	-	-	100	$\mu A$
$I_{GES}$	Gate Leakage Current, Forward	$V_{GE}=\pm 20V, V_{CE}=0V$	-	-	$\pm 100$	nA
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE}=V_{CE}, I_C=250\mu A$	5.1	-	6.9	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=30A$	-	2.0	2.5	V
$Q_g$	Total Gate Charge	$V_{CC}=480V$ $V_{GE}=15V$ $I_C=30A$	-	594		nC
$Q_{ge}$	Gate-Emitter Charge		-	119		nC
$Q_{gc}$	Gate-Collector Charge		-	374		nC
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=400V$ $V_{GE}=15V$ $I_C=30A$ $R_G=15\Omega$ Inductive Load $T_C=25^\circ\text{C}$	-	19	-	ns
$t_r$	Turn-on Rise Time		-	65	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	86	-	ns
$t_f$	Turn-off Fall Time		-	98	-	ns
$E_{on}$	Turn-on Switching Loss		-	1.3	-	mJ
$E_{off}$	Turn-off Switching Loss		-	0.5	-	mJ
$E_{ts}$	Total Switching Loss		-	1.8	-	mJ
$C_{ies}$	Input Capacitance	$V_{CE}=25V$ $V_{GE}=0V$ $f=1\text{MHz}$	-	1340	-	pF
$C_{oes}$	Output Capacitance		-	98	-	pF
$C_{res}$	Reverse Transfer Capacitance		-	11.8	-	pF

**Electrical Characteristics of Diode** ( $T_C=25^\circ\text{C}$  unless otherwise noted )

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_F$	Diode Forward Voltage	$I_F=30A$	-	1.5	3.0	V
$t_{rr}$	Diode Reverse Recovery Time	$V_{CE}=400V$ $I_F=30A$ $R_G=15\Omega$	-	148		ns
$I_{rr}$	Diode peak Reverse Recovery Current		-	13.8		A
$Q_{rr}$	Diode Reverse Recovery Charge		-	1055		nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature

## Typical Performance Characteristics

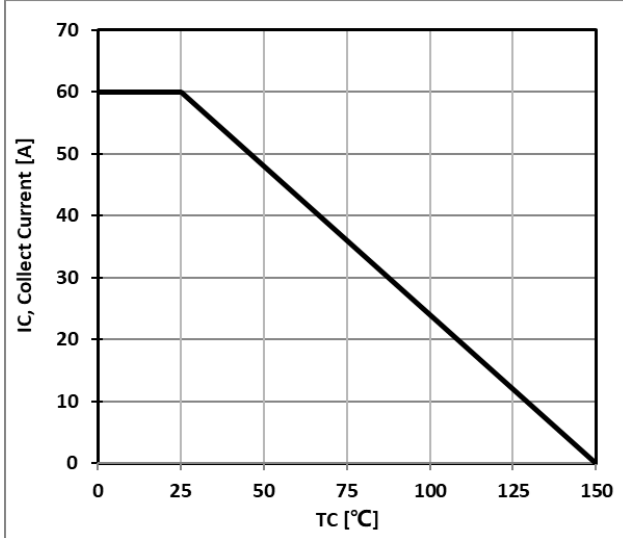


Figure 1: Maximum DC Collector Current VS. case temperature

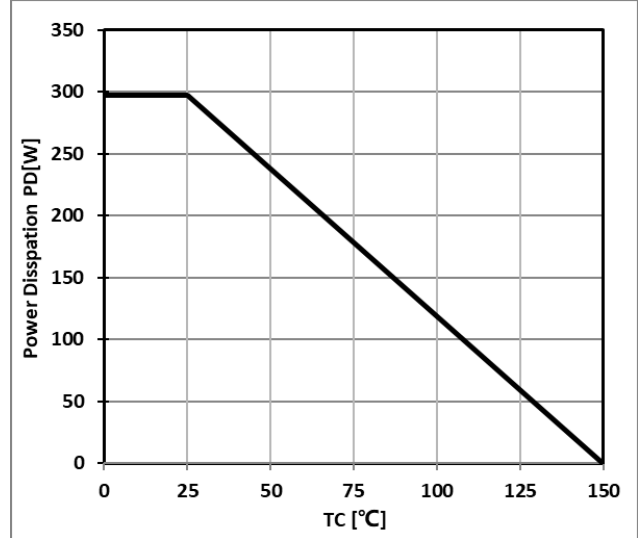


Figure 2: Power Dissipation VS. Case Temperature

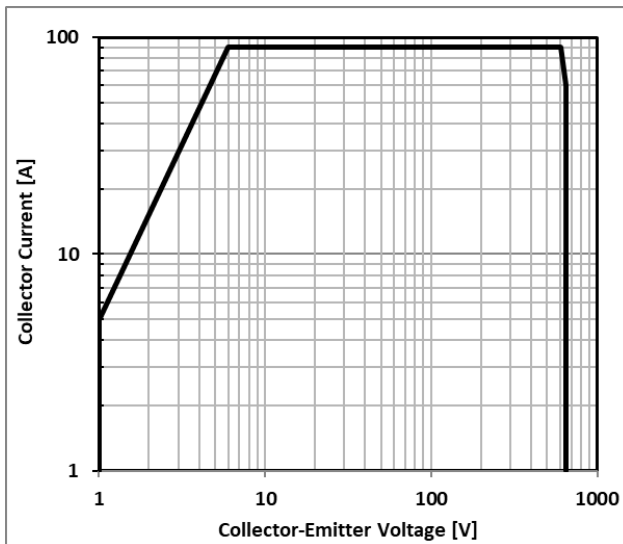


Figure 3: Reverse Bias SOA,  $T_J=125^{\circ}\text{C}$ ,  $V_{GE}=15\text{V}$

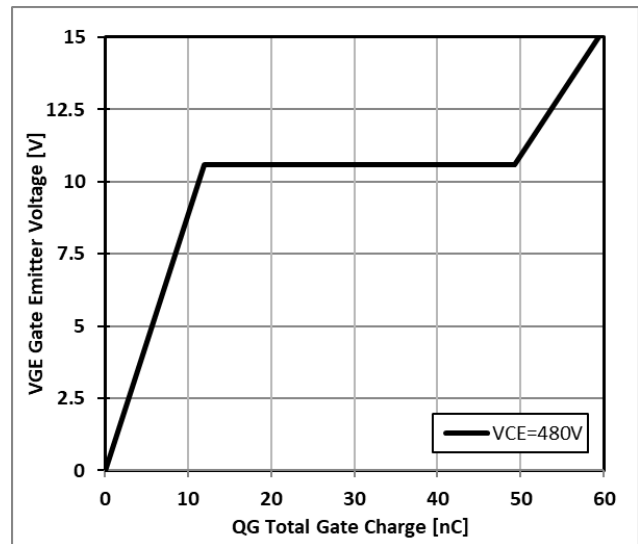


Figure 4: Typical Gate charge VS.  $V_{GE}$ ,  $I_C=30\text{A}$

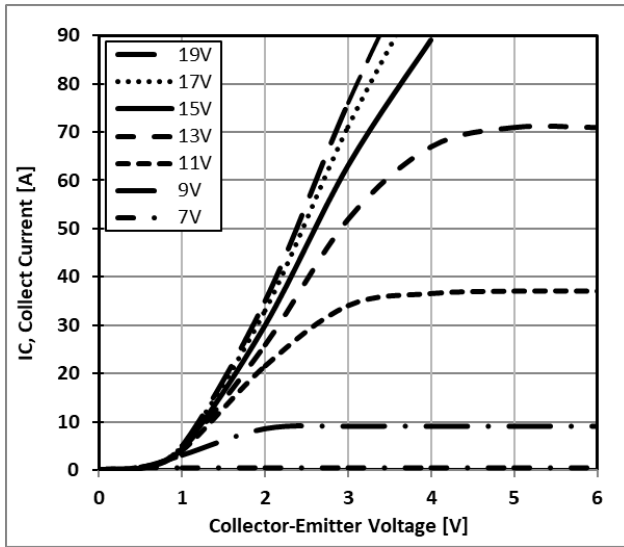


Figure 5: Typical IGBT Output characteristics,  
TC=25°C;tp=300us

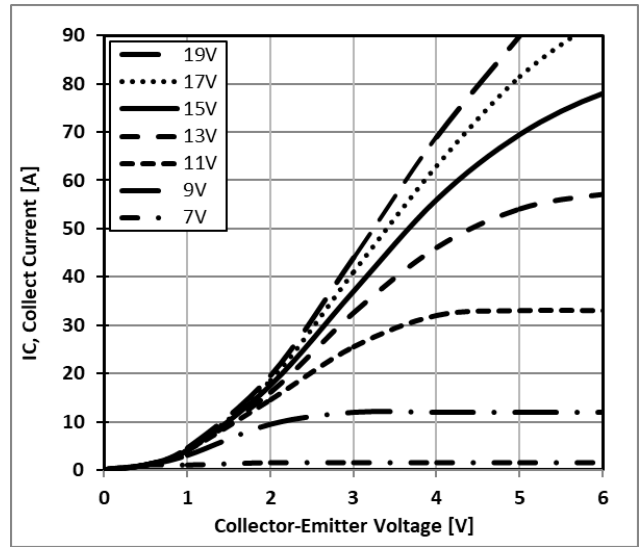


Figure 6: Typical IGBT Output characteristics,  
TC=150°C;tp=300us

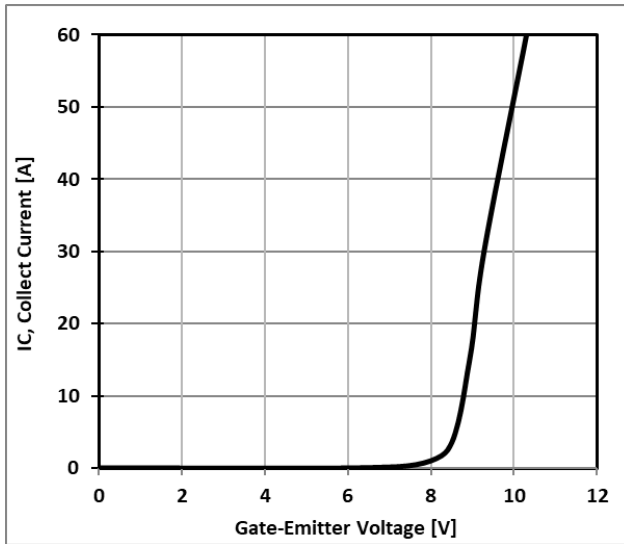


Figure 7: Typical Gate Threshold Voltage

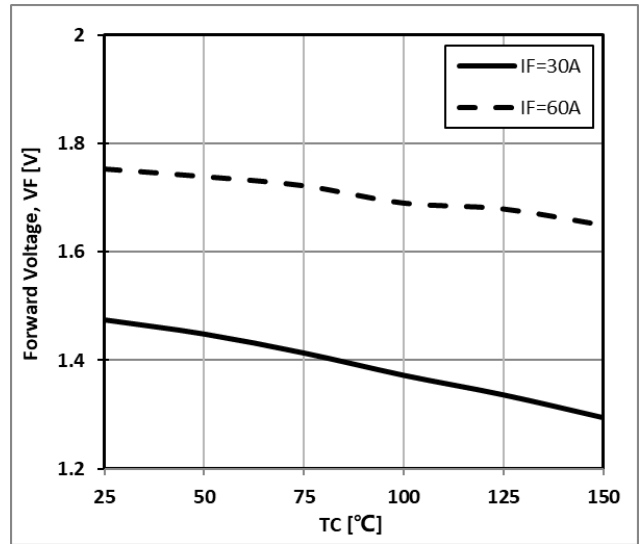


Figure 8: Typical Forward Voltage vs IF

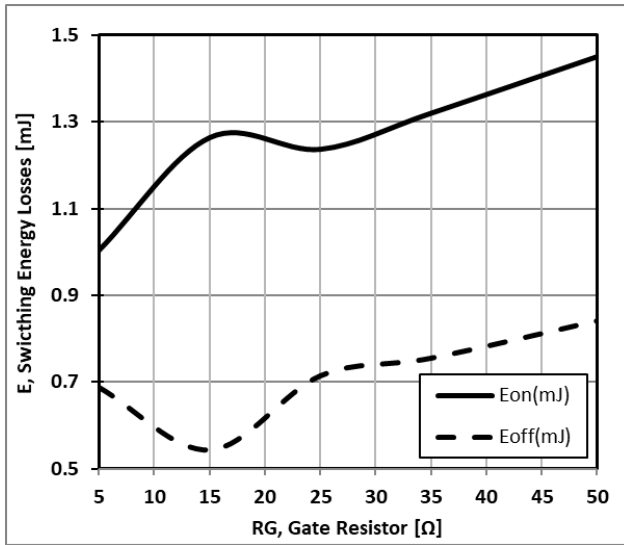


Figure 9: Typical Energy Loss VS. RG, TC=25°C,  
L=200uH, VCE=400V, VGE=15V, IC=30A

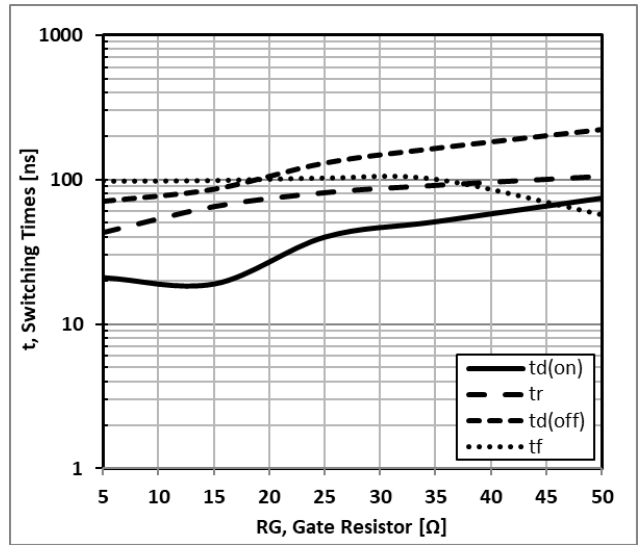


Figure 10: Typical Switching Time VS. RG, TC=25°C,  
L=200uH, VCE=400V, VGE=15V, IC=30A

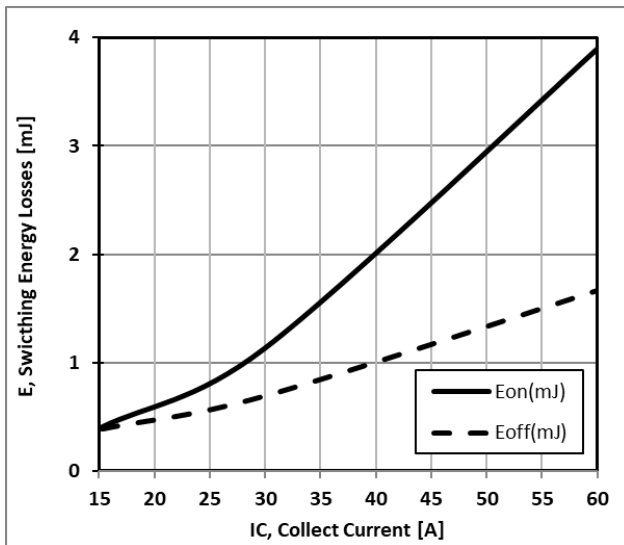


Figure 11: Typical Energy Loss VS. IC, TC=25°C,  
L=200uH, VCE=400V, VGE=15V, RG=15Ω

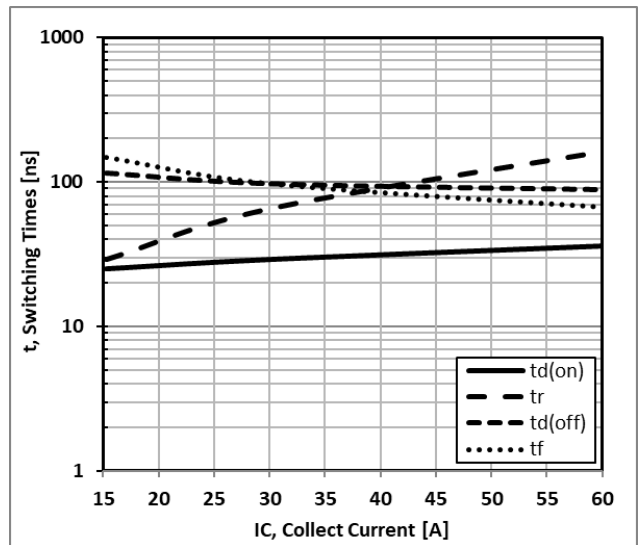


Figure 12: Typical Switching Time VS. IC, TC=25°C,  
L=200uH, VCE=400V, VGE=15V, RG=15Ω

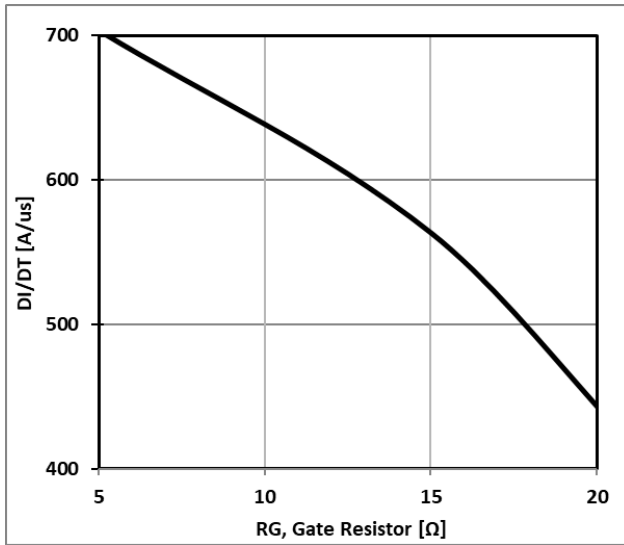


Figure 13: Typical Diode DI/DT VS. RG, TC=25°C  
VCC=400V, VGE=15V, IF=30A

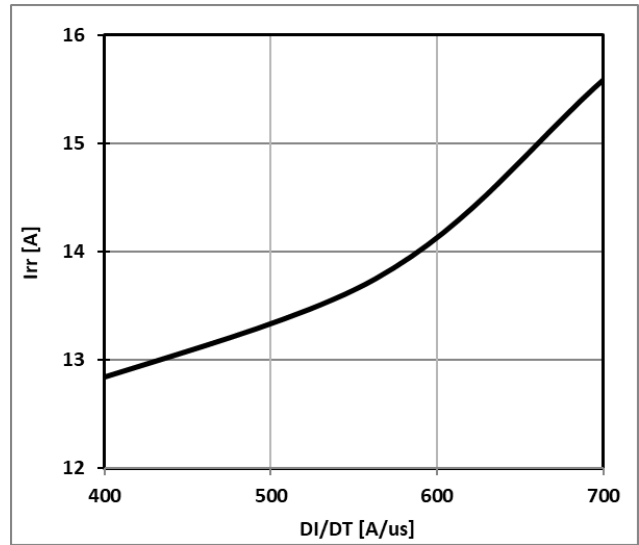


Figure 14: Typical Diode IRR VS. DI/DT, TC=25°C  
VCC=400V, VGE=15V, IF=30A

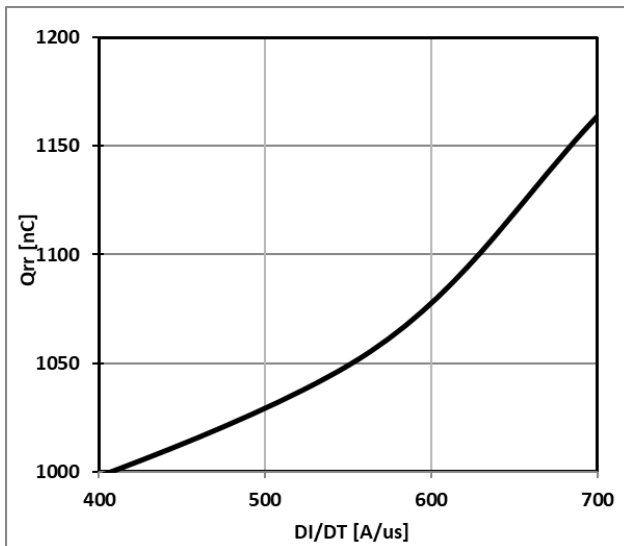


Figure 15: Typical Diode Qrr VS. DI/DT, TC=25°C  
VCC=400V, VGE=15V, IF=30A

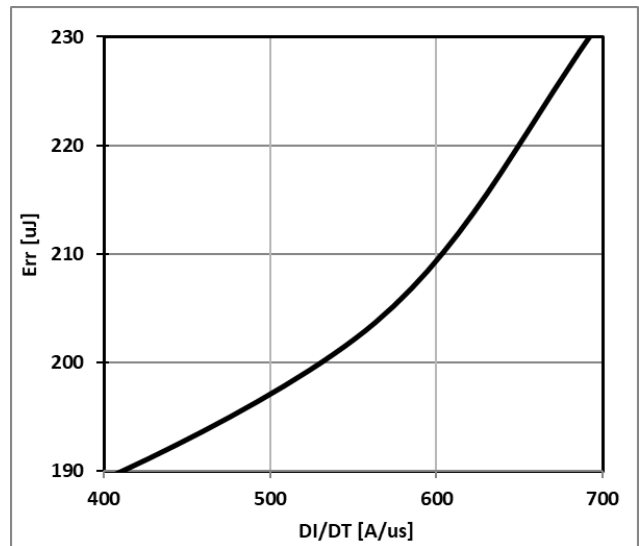


Figure 16: Typical Diode Err VS. DI/DT, TC=25°C  
VCC=400V, VGE=15V, IF=30A

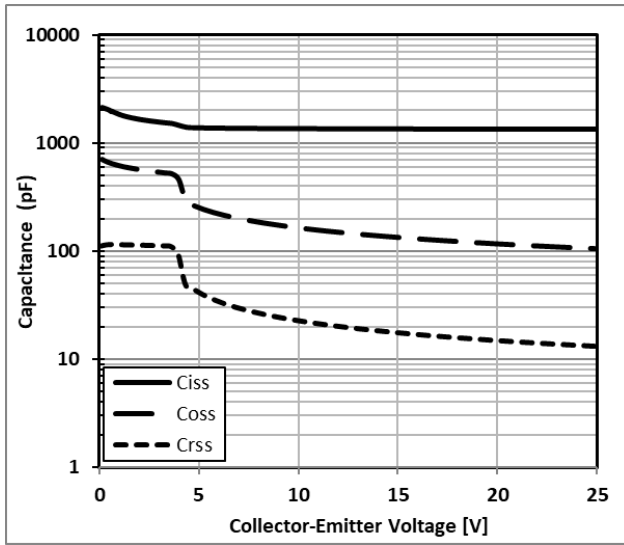


Figure 17: Typical Capacitance VS. VCE,  
VGE=0V, f=1MHz

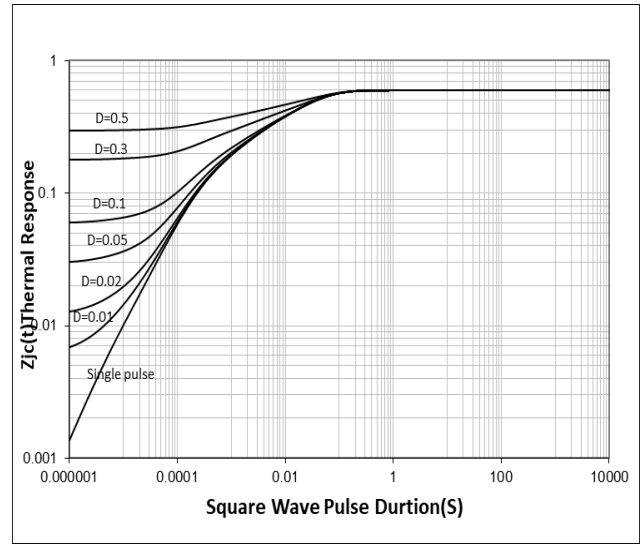
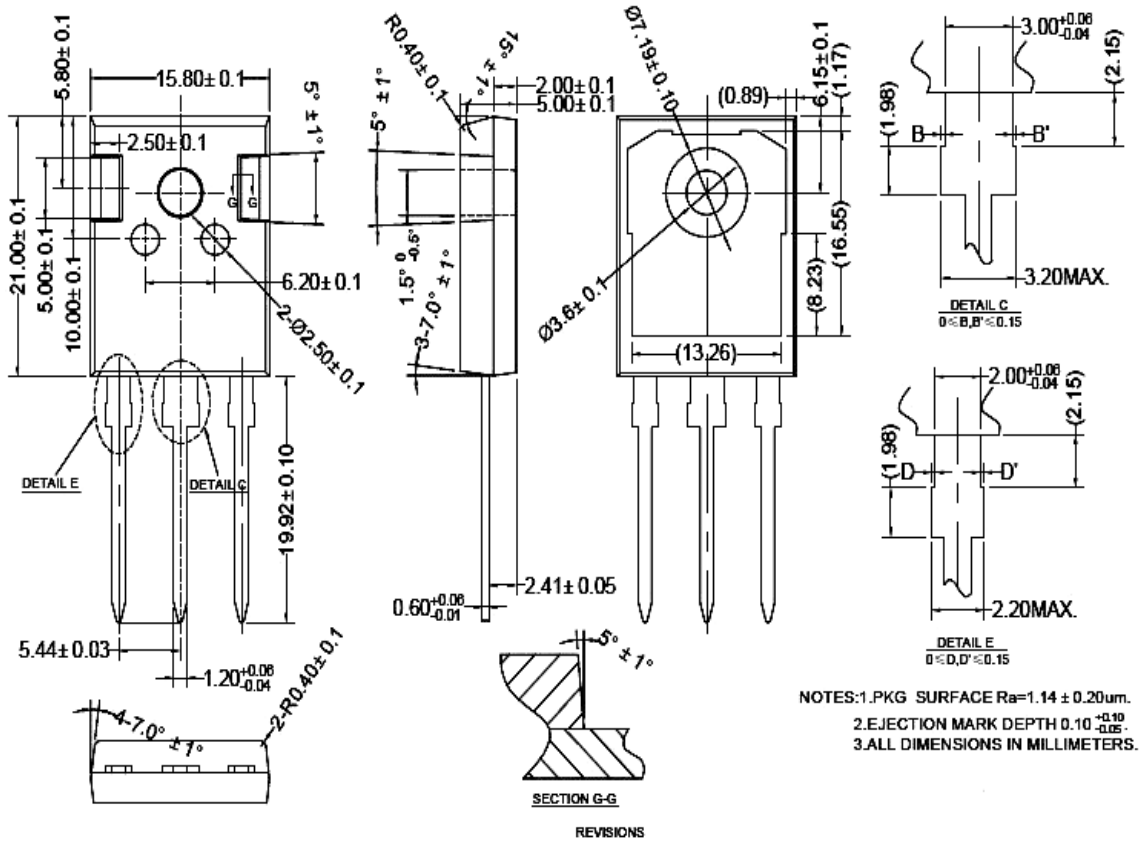


Figure 18: Normalized transient thermal impedance  
junction-to-case

TO-247 PACKAGE OUTLINE



公差标注	公差值	表面粗糙度
0	±0.2	Ra3.2~6.3
0.0	±0.1	Ra1.6~3.2
0.00	±0.01	Ra0.8~1.6
0.000	±0.005	Ra0.4~0.8
0.0000	±0.002	Ra0.2~0.4

0 ≤ D, D' ≤ 0.15

NOTES: 1. PKG SURFACE Ra=1.14 ± 0.20um.  
2. EJECTION MARK DEPTH 0.10 <sup>+0.10</sup>/<sub>-0.05</sub>.  
3. ALL DIMENSIONS IN MILLIMETERS.



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